

Triple Bonds to Silicon. Substituent Effects on the Thermodynamic and Kinetic Stabilities of Silynes Relative to Their Isomeric Silylidenes and Silavinylidenes

Yitzhak Apeloig* and Miriam Karni

Department of Chemistry and the Minerva Center for Computational Quantum Chemistry, Technion-Israel Institute of Technology, Haifa 32000, Israel

Received October 3, 1996[®]

Summary: Substituent effects on the potential energy surface (PES) of $RHSiC$ ($R = H, CH_3, SiH_3, F, OH$) were studied by *ab initio* molecular orbital methods. The unimolecular and kinetic stability of silaacylenes is strongly dependent on the substituent, pointing to $FSi\equiv CH$ and $R'OSi\equiv CH$ as viable candidates for experimental observation.

The first stable compounds with double bonds to silicon were synthesized in 1981, and since then they have been studied extensively both experimentally¹ and theoretically.² In contrast, stable compounds containing triply-bonded silicon compounds are still unknown, except for $HSi\equiv N$ which was characterized spectroscopically at 10 K.^{3a,b} Evidence for the involvement of the "synthetic equivalent" on $CH_3Si\equiv SiCH_3$ was presented recently by West et al., but the existence of a $Si\equiv Si$ bond could not be shown unequivocally.⁴

One of the major obstacles to the synthesis of triply-bonded silicon compounds even as transients results from the existence of more stable isomers, e.g., for Si_2H_2 the dibridged, monobridged, and $H_2Si=Si$: isomers are more stable than $HSi\equiv SiH$.⁵ This contrasts with C_2H_2 where acetylene is the global minimum, $H_2C=C$: is by 43 kcal/mol higher in energy, and the H-bridged species are not minima on the potential energy surface (PES).⁶

For the parent H_2CSi , structures **1–4** ($R = H$) were studied computationally.^{7–11} At the HF level only **3** ($R = H$) and **4** ($R = H$) are minima on the PES, but at correlated levels the *trans-bent*-silyne **2** ($R = H$) is also in a shallow minimum.^{7d,9,10} The linear silyne **1** ($R = H$) is not a minimum on the PES.^{7d,e,8–10} The global minimum is $H_2C=Si$: being by 86.8 and 39.2 kcal/mol (at CCSD(T)/TZ2P(f,d)¹⁰) more stable than **4** ($R = H$) and **2** ($R = H$), respectively. Relatively small barriers separate **4** ($R = H$) from **2** ($R = H$) (2.7 kcal/mol at CCSD(T)/TZ2P(f,d)¹⁰ and **2** ($R = H$) from **3** ($R = H$) (ca. 5.0 kcal/mol at QCISD(T)/6-311++G(3df,3dp)⁹ and CCSD(T)/TZ2P(f,d)¹⁰), predicting that the half-life of $HSi\equiv CH$ is ca. 10^{-8} s, suggesting that it might be observed spectroscopically.⁹ However so far only $H_2C=Si$: was detected.^{11,12}

Can substitution reverse the order of stability of **2** and **3** making the silaacylene **2** the global minimum? Or alternatively, can substitution increase the barrier for the **2** → **3** interconversion, making silynes a viable synthetic target? To answer these questions we have calculated¹³ at a highly correlated level the PES of several monosubstituted $RHSiC$ systems **2–4**, with $R = CH_3, SiH_3, F$, and OH ,¹⁴ and these calculations point to a possible strategy for the synthesis of persistent silynes.

Can substitution reverse the order of stability of **2** and **3** making the silaacylene **2** the global minimum? Or alternatively, can substitution increase the barrier for the **2** → **3** interconversion, making silynes a viable synthetic target? To answer these questions we have calculated¹³ at a highly correlated level the PES of several monosubstituted $RHSiC$ systems **2–4**, with $R = CH_3, SiH_3, F$, and OH ,¹⁴ and these calculations point to a possible strategy for the synthesis of persistent silynes.

(6) Gallo, M. M.; Hamilton, T. P.; Schaefer, H. F., III. *J. Am. Chem. Soc.* **1990**, *112*, 8714.

(7) (a) Gordon, M. S.; Pople, J. A. *J. Am. Chem. Soc.* **1981**, *103*, 2945.

(b) Gordon, M. S. *J. Am. Chem. Soc.* **1982**, *104*, 4352. (c) Hopkinson, A. C.; Lien, M. H.; Csizmadia, I. G. *Chem. Phys. Lett.* **1983**, *95*, 232.

(d) Hoffman, M. R.; Yoshioka, Y.; Schaefer, H. F., III. *J. Am. Chem. Soc.* **1983**, *105*, 1084. (e) Luke, B. T.; Pople, J. A.; Krogh-Jespersen, M.-B.; Apeloig, Y.; Karni, M.; Chandrasekhar, J.; Schleyer, P. v. R. *J. Am. Chem. Soc.* **1986**, *108*, 270.

(8) Schoeller, W. W.; Strutwolf, J. *J. Mol. Struct.* **1994**, *305*, 127.

(9) Nguyen, M. T.; Sengupta, D.; Vanquikborne, L. G. *Chem. Phys. Lett.* **1995**, *244*, 83.

(10) Stegmann, R.; Frenking, G. *J. Comput. Chem.* **1996**, *17*, 781.

(11) Sherril, D.; Schaefer, H. F., III. *J. Phys. Chem.* **1995**, *99*, 1949.

(12) (a) Damrauer, R.; DePuy, C. H.; Barlow, S. E.; Gronert, S. *J. Am. Chem. Soc.* **1988**, *110*, 2005. (b) Srinivas, R.; Sulzle, D.; Schwarz, H. *J. Am. Chem. Soc.* **1991**, *113*, 52.

(13) The calculations were carried out using the Gaussian 92 package of programs. Gaussian 92: Frisch, M. J.; Trucks, G. W.; Head-Gordon, M.; Gill, P. M. W.; Wong, M. W.; Foresman, J. B.; Johnson, B. G.; Schlegel, H. B.; Robb, M. A.; Replogle, E. S.; Goperts, R.; Andres, J. L.; Raghavachari, K.; Binkley, J. S.; Gonzalez, C.; Martin, R. L.; Fox, D. J.; Defrees, D. J.; Baker, J.; Stewart, J. J. P.; Pople, J. A. GAUSSIAN 92/DFT, Revision G; Gaussian Inc.: Pittsburgh, 1992.

(14) The calculations were carried out using the Gaussian 92 package of programs. Gaussian 92: Frisch, M. J.; Trucks, G. W.; Head-Gordon, M.; Gill, P. M. W.; Wong, M. W.; Foresman, J. B.; Johnson, B. G.; Schlegel, H. B.; Robb, M. A.; Replogle, E. S.; Goperts, R.; Andres, J. L.; Raghavachari, K.; Binkley, J. S.; Gonzalez, C.; Martin, R. L.; Fox, D. J.; Defrees, D. J.; Baker, J.; Stewart, J. J. P.; Pople, J. A. GAUSSIAN 92/DFT, Revision G; Gaussian Inc.: Pittsburgh, 1992.

[®] Abstract published in *Advance ACS Abstracts*, January 15, 1997.

(1) (a) For a comprehensive overview see: Raabe, G.; Michl, J. In *The Chemistry of Organic Silicon Compounds*; Patai, S., Rappoport, Z., Eds.; John Wiley: New York, 1989; Chapter 17, p 1015. (b) Kira, M.; Maruyama, T.; Kabuto, C.; Ebata, K.; Sakurai, H. *Angew. Chem., Int. Ed. Engl.* **1994**, *33*, 1489. (c) Okazaki, R.; West, R. *Adv. Organomet. Chem.* **1996**, *39*, 231. (d) For synthetic studies on $Si=N$, $Si=P$, $Si=As$, and $Si=S$ the reader is referred to: (i) Hesse, M.; Klingebiel, U. *Angew. Chem., Int. Ed. Engl.* **1986**, *25*, 649. (ii) Driess, M. *Angew. Chem., Int. Ed. Engl.* **1991**, *30*, 1022. Bender, H. R. G.; Niecke, E.; Nieger, M. *J. Am. Chem. Soc.* **1993**, *115*, 3314. (iii) Driess, M.; Pritzkow, H. *Angew. Chem., Int. Ed. Engl.* **1992**, *31*, 816. (iv) Suzuki, H.; Tokitoh, N.; Nagase, S.; Okazaki, R. *J. Am. Chem. Soc.* **1994**, *116*, 11578.

(2) (a) Apeloig, Y. In *The Chemistry of Organic Silicon Compounds*; Patai, S., Rappoport, Z., Eds.; John Wiley: New York, 1989; pp 57–225.

(3) (a) Maier, G.; Glatthaar, J. *Angew. Chem., Int. Ed. Engl.* **1994**, *33*, 473. (b) Transient isonitriles $HNSi^{\delta-}C$ and $PhNSi^{\delta-}C$ have also been characterized spectroscopically, but those can be regarded as possessing a formal $N=Si$ double bond;^{3c} the presence of $PhNSi$ and $PhSiN$ was suggested by trapping reactions.^{3f} (c) Goldberg, N.; Iraqui, M.; Hrusak, J.; Schwarz, H. *Int. J. Mass Spectrometry Ion Processes* **1993**, *125*, 267. Ogilvie, J. F.; Cradock, S. J. *J. Chem. Soc., Chem. Commun.* **1966**, 364. (d) Bock, H.; Dammel, R. *Angew. Chem., Int. Ed. Engl.* **1985**, *24*, 111. (e) Apeloig, Y.; Albrecht, K. *J. Am. Chem. Soc.* **1995**, *117*, 7263. (f) Radziszewski, J. G.; Littmann, D.; Balaji, V.; Fabry, L.; Gross, G.; Michl, J. *Organometallics* **1993**, *12*, 4816.

(4) Sekiguchi, A.; Gillette, G. R.; West, R. *Organometallics* **1988**, *7*, 1226.

(5) Koseki, S.; Gordon, M. S. *J. Phys. Chem.* **1988**, *92*, 364. Koseki, S.; Gordon, M. S. *J. Phys. Chem.* **1989**, *93*, 118. Colgrove, B. T.; Schaefer, H. F., III. *J. Phys. Chem.* **1990**, *94*, 5593. Grev, R.; Schaefer, H. F., III. *J. Chem. Phys.* **1992**, *97*, 7990.

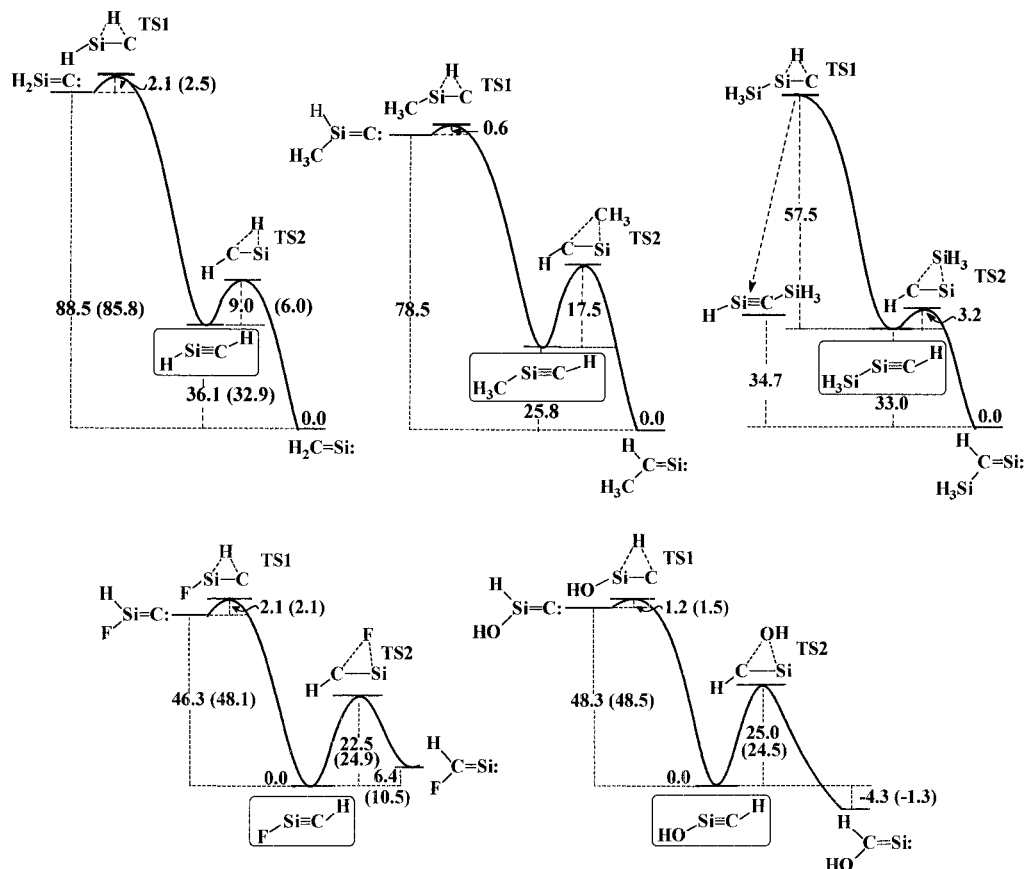


Figure 1. Potential energy surfaces for RHCSi , $\text{R} = \text{H}, \text{CH}_3, \text{SiH}_3, \text{F},$ and OH . Energies are in kcal/mol, calculated at $\text{MP4SDTQ}/6\text{-}31\text{G}(\text{d},\text{p})//\text{MP2}/6\text{-}31\text{G}(\text{d},\text{p}) + \text{ZPE}$; the values in parentheses are at $\text{QCISD}(\text{T})/6\text{-}31\text{G}(\text{d},\text{p})//\text{QCISD}/6\text{-}31\text{G}(\text{d},\text{p}) + \text{ZPE}$ (ZPE calculated numerically).

The geometries of all stationary points were fully optimized and characterized by their Hessian matrices at $\text{MP2}/6\text{-}31\text{G}(\text{d},\text{p})$ and for $\text{R} = \text{F}$ and OH also at $\text{QCISD}/6\text{-}31\text{G}(\text{d},\text{p})$.¹³ The optimized geometries of **2a**, **2b**, **3**, and **4** and of the transition structures separating **2b** from **4** (TS1) and from **3** (TS2) for $\text{R} = \text{H}, \text{CH}_3, \text{SiH}_3, \text{OH},$ and F are given in Table 1 of the Supporting Information. Single point energies at these optimized geometries were calculated at $\text{MP4SDTQ}/6\text{-}31\text{G}(\text{d},\text{p})//\text{MP2}/6\text{-}31\text{G}(\text{d},\text{p})$ and at $\text{QCISD}(\text{T})/6\text{-}31\text{G}(\text{d},\text{p})//\text{QCISD}/6\text{-}31\text{G}(\text{d},\text{p})$ (Tables 2 and 3, Supporting Information).

The PES of H_2SiC was restudied in detail (including geometry optimizations at $\text{MP2}/6\text{-}31\text{G}(\text{d},\text{p})$, $\text{MP2}/6\text{-}31\text{G}(2\text{df},\text{p})$, and $\text{MP2}/6\text{-}311\text{G}(\text{d},\text{p})$), and the results (Table 4, Supporting Information) indicate that addition of a second set of d or f polarization functions or further splitting of the valence shell all have a minor effect on the relative energies of the **2–4** ($\text{R} = \text{H}$) isomers and on the barriers for their interconversion. The reasonably good agreement between the experimental¹¹ and the calculated harmonic vibrational frequencies¹⁵ of $\text{H}_2\text{C}=\text{Si}$: (Table 5, Supporting Information) lends confidence in the reliability of the computational methods that are used in this study.

(14) For previous lower level HF studies on the effect of substituents on $\text{RR}'\text{SiC}$: see the following. (a) For Li, Me, and F at $\text{HF}/6\text{-}31\text{G}^*/3\text{-}21\text{G}$ (stationary points were not characterized), see ref 7c. (b) For CSiF_2 at $\text{HF}/6\text{-}31\text{G}^*/3\text{-}21\text{G}$, see ref 7b.

(15) The best experimental–theoretical agreement is obtained using the $\text{MP2}/6\text{-}31\text{G}(2\text{df},\text{p})$ optimized geometries. However as the relative energies of **2–4** ($\text{R} = \text{H}$) are hardly affected by increasing the basis set, we assume that $\text{MP4SDTQ}/6\text{-}31\text{G}(\text{d},\text{p})//\text{MP2}/6\text{-}31\text{G}(\text{d},\text{p})$ calculations can be used for estimating reliably the relative energies of the various stationary points on the RHSiC PES.

The calculated PES for RHCSi , $\text{R} = \text{H}, \text{CH}_3, \text{SiH}_3, \text{F},$ and OH , at $\text{MP4SDTQ}/6\text{-}31\text{G}(\text{d},\text{p})//\text{MP2}/6\text{-}31\text{G}(\text{d},\text{p})$ and at $\text{QCISD}(\text{T})/6\text{-}31\text{G}(\text{d},\text{p})//\text{QCISD}/6\text{-}31\text{G}(\text{d},\text{p})$ are shown in Figure 1.^{16,17} The “classical” linear silynes **1** are not minima on the PES for all systems. Their two imaginary frequencies lead to the corresponding *trans*-bent-silyne minima, whose energies relative to the other isomers change significantly with substitution.

Silyl has a very small effect on the relative stabilities of the RHSiC isomers: **3** remains the global minimum, and the silynes **2a**, **b** are by 34.7 and 33.0 kcal/mol less stable than the corresponding silylidene. A methyl causes a somewhat larger effect, but the silylidene **3** is still by 28.6 and 25.8 kcal/mol more stable than **2a**, **b**, respectively. However, the kinetic stability of **2b** is quite strongly affected by these substituents. Thus, for $\text{R} = \text{CH}_3$ the barrier for the **2b** → **3** isomerization increases by 8.5 kcal/mol (relative to $\text{R} = \text{H}$) to 17.5 kcal/mol, making $\text{CH}_3\text{Si}=\text{CH}$ relatively stable kinetically if it were produced. On the other hand, for $\text{R} = \text{SiH}_3$, the **2b** → **3** barrier decreases to only 3.2 kcal/mol and the data in Figure 1 suggest that at higher computational levels it will be smaller or will even disappear, questioning the possible existence of **2b**, $\text{R} = \text{SiH}_3$. In contrast, the effect of F and OH on the relative stabilities of $\text{RSi}=\text{CH}$ (**2b**) and $\text{RHC}=\text{Si}$: (**3**) is very large. F actually reverses the stability order and $\text{FSi}=\text{CH}$ (**2b**) is the global minimum on the PES, being by 6.4 kcal/mol (10.5

(16) Relative energies in the text are given at the $\text{MP4SDTQ}/6\text{-}31\text{G}^*/\text{MP2}/6\text{-}31\text{G}^* + \text{ZPE}$ level unless otherwise stated.

(17) For all systems the effect of entropy on the relative energies of the isomers is very small, and ΔG is therefore very similar to the relative energies given in Figure 1.

kcal/mol at QCISD(T)/6-31G**//QCISD/6-31G** + ZPE) more stable than HFC=Si: For R = OH, **3** is still more stable than **2b**, but by only 4.3 kcal/mol (1.3 kcal/mol at QCISD(T)/6-31G**//QCISD/6-31G** + ZPE). These large effects are best understood in terms of the R–Si vs R–C bond energies, where the very strong Si–F and Si–O bonds (bond dissociation energies: Si–F = 152 kcal/mol, Si–O = 129 kcal/mol,¹⁸ C–F = 110 kcal/mol, C–O = 92.2¹⁹) override the large intrinsic preference of H₂C=Si: over HSi≡CH. The strong Si–F and Si–O bonds also dictate the higher stability of RSi≡CH relative to HSi≡CR (by 33.4 and 23.4 kcal/mol for R = F and OH, respectively).

F and OH substitution also dramatically stabilizes kinetically the silynes **2b**. Thus, the barrier for the isomerization of **2b** to **3** (Figure 1) increases from only 9.0 kcal/mol for R = H to 22.5 and 25.0 kcal/mol for R = F and OH respectively (24.9 and 24.5 kcal/mol, respectively, at QCISD(T)/6-31G(d,p)//QCISD/6-31G(d,p) + ZPE). Consequently we predict that if FSi≡CH, and HOSi≡CH will be generated (e.g., in a matrix), their rearrangement to the corresponding RHC=Si: isomers will be slow even at relatively high temperatures.²⁰ The same should apply to systems such as FSi≡CR or R'OSi≡CR', where R, R', or R'' = alkyl or aryl.

The calculated Si≡C bond lengths of RSi≡CH (**2b**) are 1.632 Å (R = H), 1.651 Å (R = F), and 1.658 Å (R = OH) at MP2/6-31G(d,p) and 1.673 Å (R = H), 1.692 Å (R = F), and 1.685 Å (R = OH) at QCISD/6-31G(d,p).²¹ These distances are significantly shorter than *r*(Si=C) in the corresponding RHSi=CH₂, i.e., 1.714 Å (R = H), 1.695 Å (R = F), and 1.700 Å (R=OH) at MP2/6-31G(d,p) (although they are longer than those calculated for the corresponding linear silynes **1** of 1.609, 1.586, and 1.590 Å, respectively (MP2/6-31G(d,p))), indicating the presence of a Si≡C bond. The calculated Si≡C harmonic stretching frequencies of **2b** (Table 6 of the Supporting Information), which are 1224 cm⁻¹ (R = H), 1218 cm⁻¹ (R = F), and 1200 cm⁻¹ (R = OH) (1012, 1082, and 1068 cm⁻¹ for the corresponding silenes, respectively), and the natural resonance theory (NRT)^{22a} and Wiberg's^{22b} bond orders (in natural atomic orbital basis) also support the presence of a Si≡C triple bond in **2b**; i.e., for trans-bent HSi≡CH, FSi≡CH, and HOSi≡CH the NRT and Wiberg's (in parentheses) bond orders are 2.93 (2.51), 2.80 (2.39), and 2.76 (2.33),^{22c} respectively (very similar values were calculated for the corresponding linear **1**), compared to 2.01 (1.65), 1.93 (1.54), and 1.90 (1.52) in the corresponding silenes.

(18) Walsh, R. In ref 1a, pp 371–391.

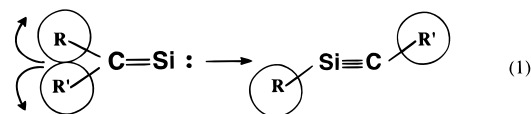
(19) Ochterski, J. W.; Peterson, G. A.; Wiberg, K. B. *J. Am. Chem. Soc.* **1995**, *117*, 11299.

(20) (a) H-rearrangements converting RSi≡CH to HRSi=C: have very high barriers (ca. 50 kcal/mol), and therefore they are not viable disappearance channels for the silynes (Figure 1). (b) FHSi=C: and (HO)HSi=C: are predicted to rearrange rapidly to FSi≡CH and HOSi≡CH, respectively (Figure 1).

(21) The longer bond lengths calculated at QCISD/6-31G(d,p) reflect the contribution of biradical configurations to the wavefunction. On the basis of the best available calculations for **2** (R = H) (at CCSD(T)/TZ2P), it was recently suggested¹⁰ that the correct Si≡C bond length is 1.65–1.66 Å, a value which is intermediate between our MP2 and QCISD values.

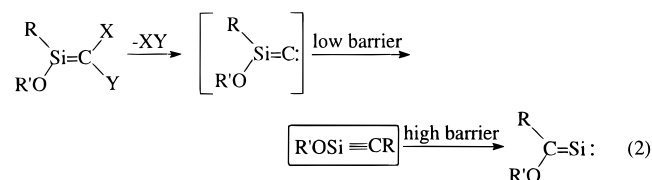
(22) (a) Weinhold, F. NBO 4.0 Program Manual, 1996. Glendening, E. D.; Weinhold, F. *J. Comput. Chem.* **1996**, submitted for publication. (b) Wiberg, K. B. *Tetrahedron* **1968**, *24*, 1083. Mayer, I. *Chem. Phys. Lett.* **1983**, *97*, 270. (c) The covalent and ionic (in parentheses) contributions to the NRT bond orders of **2b**, R = H, F, and OH, are 2.31 (0.62), 2.06 (0.74), and 2.05 (0.71), respectively. The Wiberg bond orders correspond only to the covalent contribution to the NRT bond orders.

Bulky substituents are expected to destabilize RR'C=Si: relative to RSi≡CR' as shown schematically in eq 1. In addition, the presence of very bulky substituents at both ends of the silyne may protect the triple bond from intermolecular reactions such as dimerization. How large are such steric effects?



Calculations (using BLYP/6-31G(d,p)//BLYP/6-31G(d,p)) of the (**2**–**3**) energy difference (ΔE) show that ΔE is reduced from 21.2 kcal/mol for R = R' = Me to 13.9 kcal/mol for R = R' = *t*-Bu. The effect of R = OMe, R' = *t*-Bu is much smaller; ΔE is reduced by only 1.3 kcal/mol relative to R = OMe, R' = Me. However, the initial ΔE for HC≡SiOH is small (Figure 1). Bulkier substituents such as *t*-Bu(CH₃)₂C and 2,4,6-tri-*tert*-butylphenyl or 2,4,6-tris[bis(trimethylsilyl)methyl]phenyl^{23,24} will reduce ΔE further and may even reverse the stability order making alkoxy-, alkyl- or arylsilynes with bulky substituents attractive candidates for detection and isolation.

A possible promising strategy, suggested by the calculations for the synthesis of a relatively stable alkoxy-silyne, is based on the high energy of the alkoxy-silavinylidene (**4**, R = R' = H) and the low barrier for its rearrangement,^{20b} suggesting that if a silavinylidene is generated (photochemically or thermally), it would rearrange spontaneously to the more stable silyne which should survive (e.g., in a matrix) as it is separated by a significant barrier from further rearrangements (eq 2).



Acknowledgment. We are grateful to Professor Robert West for many helpful discussions. The financial support of the U.S.-Israel Binational Science Foundation (BSF), of the German Federal Ministry for Science, Research, Technology, and Education (BMBF) and the Minerva Foundation in Munich, and of the Vice-President Fund for the Promotion of Research at the Technion is gratefully acknowledged.

Supporting Information Available: Tables 1–6, listing optimized geometrical parameters of the stationary points on the RHSiC PES, absolute energies for stationary points on the RHSiC PES, relative energies of stationary points on the PES of RHCSi, relative energies of H₂SiC isomers and the barriers for their interconversion, calculated harmonic and experimental fundamental vibrational frequencies of H₂C=Si:, and harmonic vibrational frequencies for RSiCH and RHC=Si: (at MP2/6-31G(d,p)) (10 pages). Ordering information is given on any current masthead page.

OM960844K

(23) For R = R' = Ph, Δ is relatively high (18.9 kcal/mol) because the phenyl rings in **3** can rotate to minimize their steric interactions. However, bulky ortho-substituents may change this situation.

(24) Tokitoh, N.; Suzuki, H.; Okazaki, R.; Ogawa, K. *J. Am. Chem. Soc.* **1993**, *115*, 10428.